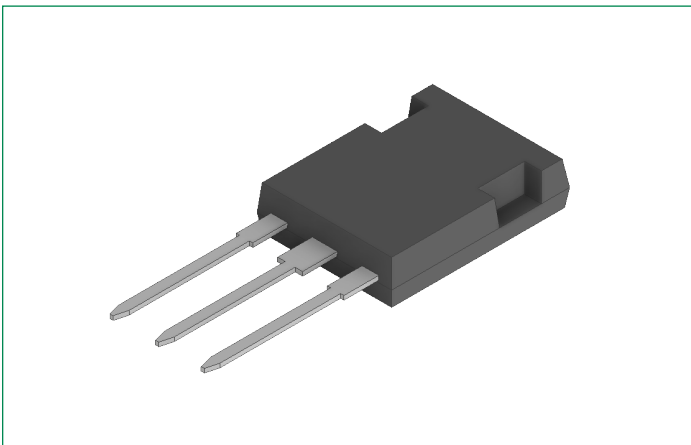


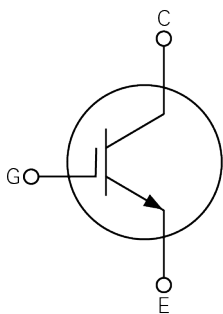
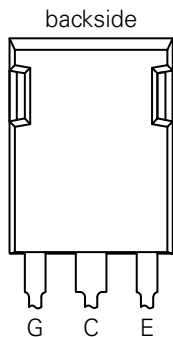
IXYX200N65B5

650 V, 200 A Gen5 XPT™ IGBT

Extreme Light Punch Through IGBT for 5–30 kHz Switching



Pinout Diagram (PLUS-247-3L)



G: Gate; **C:** Collector; **E:** Emitter; **backside:** Collector

Description:

Developed using our proprietary XPT™ thin-wafer technology and state-of-the-art Trench IGBT process, these devices feature reduced thermal resistance, optimization for medium switching applications and high power density.

Features & Benefits:

- Optimized for 5–30 kHz Switching
- Positive Thermal Coefficient of $V_{CE(sat)}$
- Square RBSOA
- International Standard Package
- High Surge Current Capability
- Low Gate Charge Q_G

Applications:

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines

Product Summary

Characteristic	Value	Unit
V_{CES}	650	V
I_{C110}	200	A
$V_{CE(sat)}$	1.45	V
$t_{fi(typ)}$	65	ns

Maximum Ratings

Symbol	Characteristic	Conditions	Value	Unit
V_{CES}	Collector-Emitter Voltage	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	650	V
V_{GES}	Gate-Emitter Voltage	Continuous	± 20	V
V_{GEM}	Transient Gate-Emitter Voltage	Transient	± 30	V
I_{C25}	Continuous Collector Current	$T_C = 25^\circ\text{C}$	470	A
I_{LRMS}	Terminal Current Limit	–	160	A
I_{C110}	Continuous Collector Current	$T_C = 110^\circ\text{C}$	210	A
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	1130	A
SSOA (RBSOA)	Switching Safe Operating Area (Reverse Biased Safe Operating Area)	$V_{GE} = 15 \text{ V}, T_{VJ} = 150^\circ\text{C}, R_G = 3 \Omega,$ Clamped Inductive Load, $I_{CM} @ V_{CE} \leq V_{CES}$	300	A
P_C	Collector Power Dissipation	$T_C = 25^\circ\text{C}$	1610	W
T_J	Junction Temperature	–	-55 to 175	$^\circ\text{C}$
T_{JM}	Maximum Junction Temperature	–	175	$^\circ\text{C}$
T_{stg}	Storage Temperature	–	-55 to 175	$^\circ\text{C}$
T_L	Lead Temperature for Soldering	1.6 mm (0.062 in.) from Case for 10 s	300	$^\circ\text{C}$
F_C	Mounting Force	–	20.. 120/4.5 ..27	N/lb
W	Weight	–	6	g

Thermal Characteristics

Symbol	Characteristic	Value			Unit
		Min.	Typ.	Max.	
$R_{th,JC}$	Thermal Resistance, junction-to-case	–	–	0.093	$^\circ\text{C/W}$
$R_{th,CS}$	Thermal Resistance, case-to-heat sink	–	0.15	–	$^\circ\text{C/W}$

Electrical Characteristics – Static ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
BV_{CES}	Collector-Emitter Breakdown Voltage	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	650	–	–	V
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 4 \text{ mA}, V_{CE} = V_{GE}$	3.7	–	5.8	V
I_{GES}	Gate-Emitter Leakage Current	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$	–	–	± 200	nA
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE} = V_{CES}, V_{GE} = 0 \text{ V}$	–	–	25	μA
		$V_{CE} = V_{CES}, V_{GE} = 0 \text{ V}, T_J = 150^\circ\text{C}$	–	–	2	mA
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ¹	$I_C = 100 \text{ A}, V_{GE} = 15 \text{ V}$	–	1.20	1.45	V
		$I_C = 100 \text{ A}, V_{GE} = 15 \text{ V}, T_J = 150^\circ\text{C}$	–	1.25	–	V

Note 1: Pulse test, $t \leq 300 \mu\text{s}$, duty cycle, $d \leq 2\%$

Electrical Characteristics – Dynamic ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Conditions	Value			Unit	
			Min.	Typ.	Max.		
g_{fs}	Transconductance ¹	$I_C = 60\text{ A}, V_{CE} = 10\text{ V}$	72	120	–	S	
C_{ies}	Input Capacitance	$V_{GE} = 0\text{ V}, V_{CE} = 25\text{ V}, f = 1\text{ MHz}$	–	11.7	–	pF	
C_{oes}	Output Capacitance		–	570	–		
C_{res}	Reverse Transfer Capacitance		–	430	–		
$Q_{g(on)}$	Total Gate Charge	$V_{GE} = 15\text{ V}, V_{CE} = 0.5 \times V_{CES},$ $I_C = 200\text{ A}$	–	790	–	nC	
Q_{ge}	Gate-Emitter Charge		–	82	–		
Q_{gc}	Gate-Collector Charge		–	376	–		
$t_{d(on)}$	Turn-on Delay Time ²	Inductive Load, $V_{GE} = 15\text{ V},$ $V_{CE} = 300\text{ V},$ $I_C = 100\text{ A},$ $R_{G(ext)} = 1\ \Omega$	$T_J = 25^\circ\text{C}$	–	77	–	ns
			$T_J = 150^\circ\text{C}$	–	60	–	
t_{ri}	Turn-on Rise Time ²		$T_J = 25^\circ\text{C}$	–	70	–	ns
			$T_J = 150^\circ\text{C}$	–	65	–	
E_{on}	Turn-on Energy ²		$T_J = 25^\circ\text{C}$	–	0.60	–	mJ
			$T_J = 150^\circ\text{C}$	–	1.40	–	
$t_{d(off)}$	Turn-off Delay Time ²		$T_J = 25^\circ\text{C}$	–	470	–	ns
			$T_J = 150^\circ\text{C}$	–	380	–	
t_{fi}	Turn-off Fall Time ²		$T_J = 25^\circ\text{C}$	–	65	–	ns
			$T_J = 150^\circ\text{C}$	–	110	–	
E_{off}	Turn-off Energy ²	$T_J = 25^\circ\text{C}$	–	3.40	–	mJ	
		$T_J = 150^\circ\text{C}$	–	4.50	–		

Note 1: Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle, $d \leq 2\%$

Note 2: Switching times and energy losses may increase for higher $V_{CE(clamp)}$, T_J , or R_G .

Characteristic Curves

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

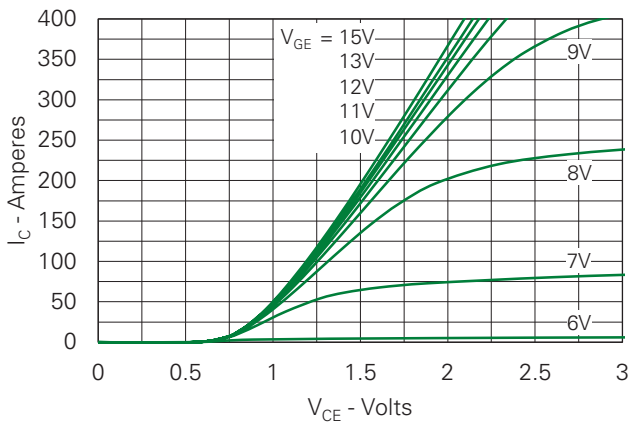


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

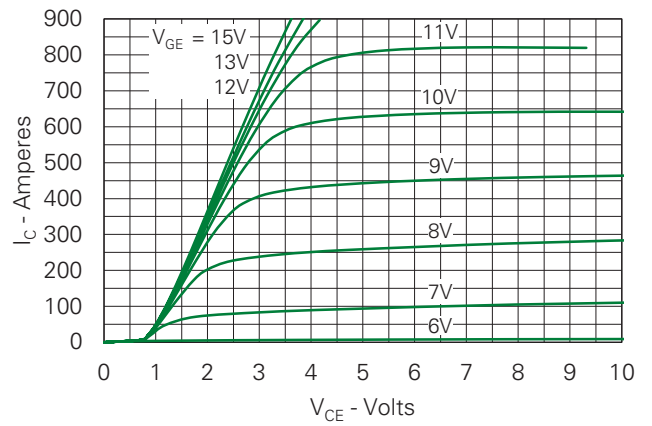


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

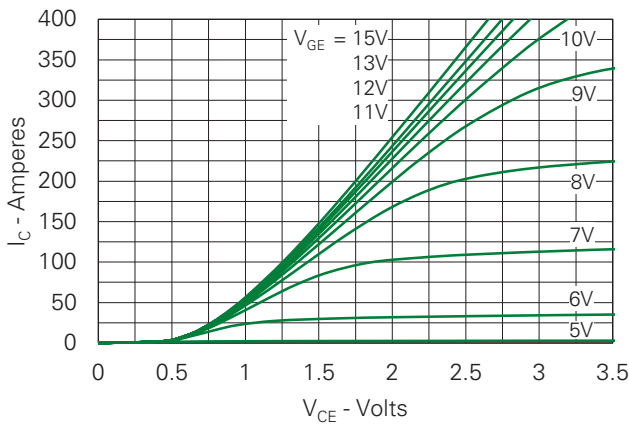


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

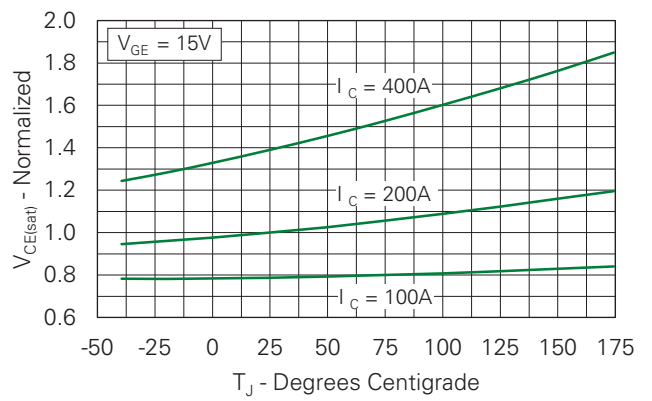


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

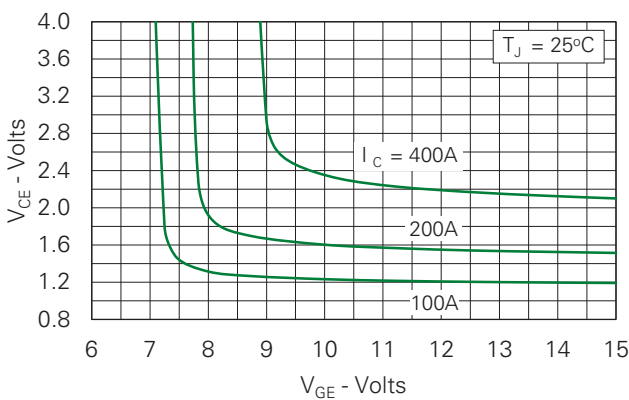


Fig. 6. Input Admittance

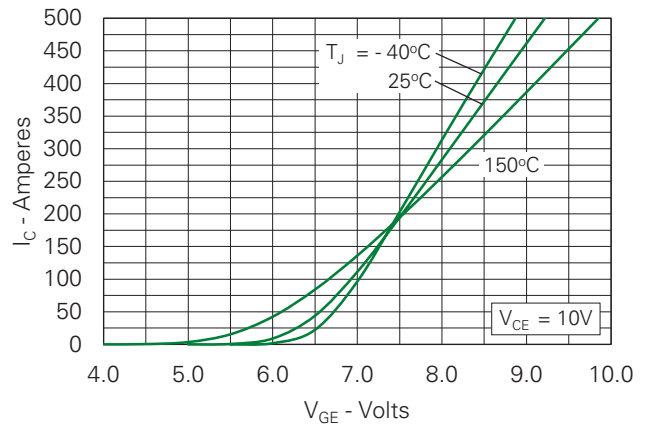


Fig. 7. Transconductance

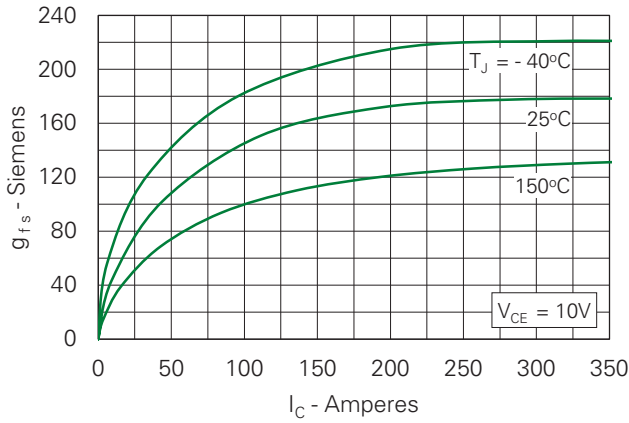


Fig. 8. Gate Charge

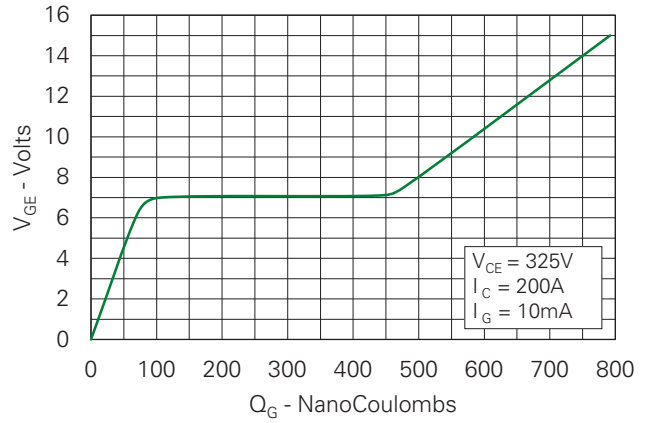


Fig. 9. Capacitance

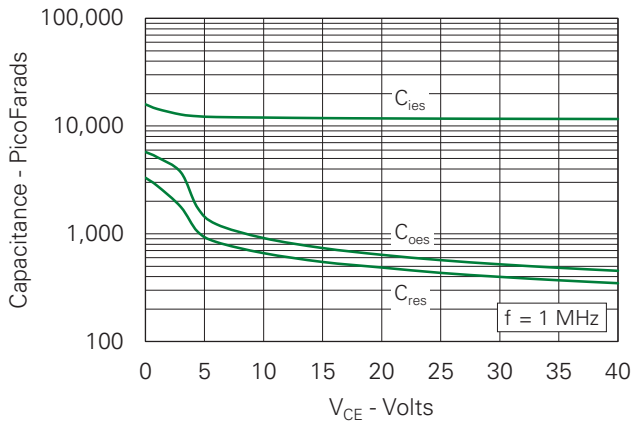


Fig. 10. Reverse-Bias Safe Operating Area

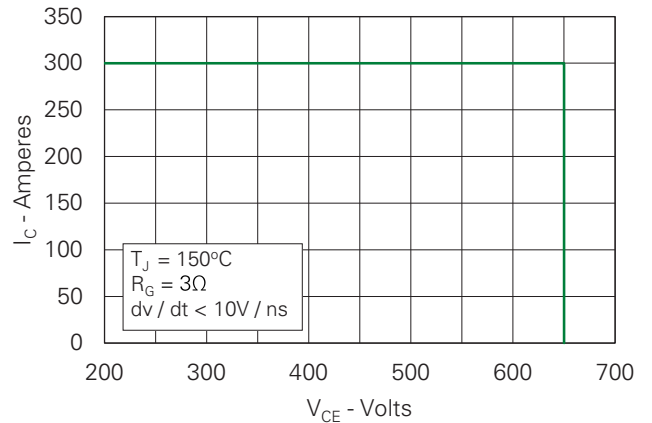


Fig. 11. Maximum Transient Thermal Impedance

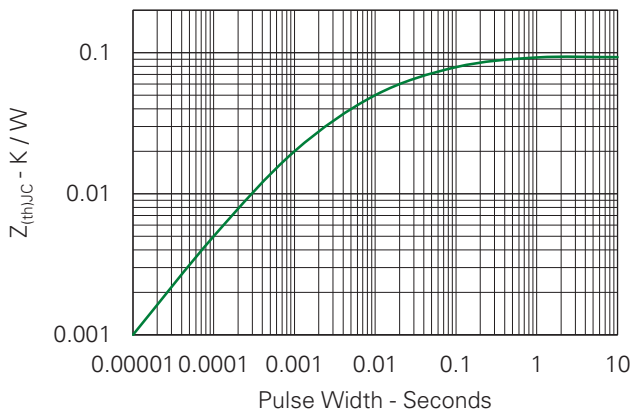


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

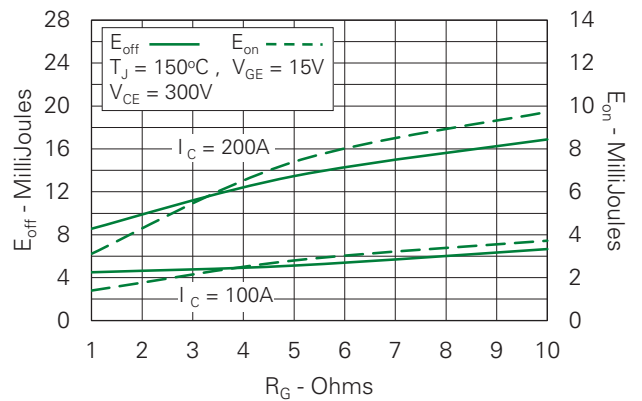


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

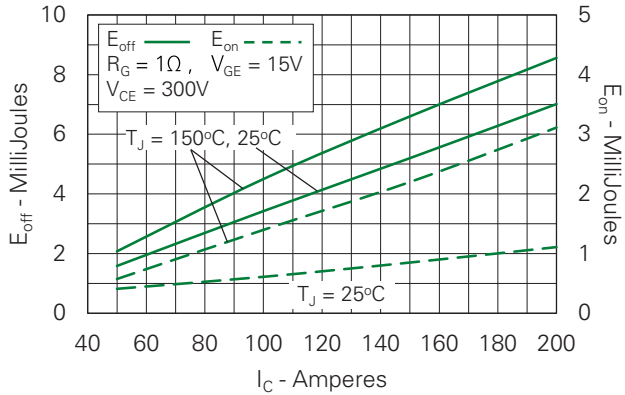


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

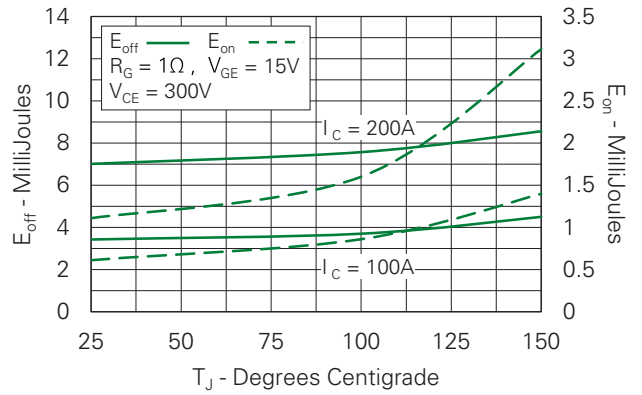


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

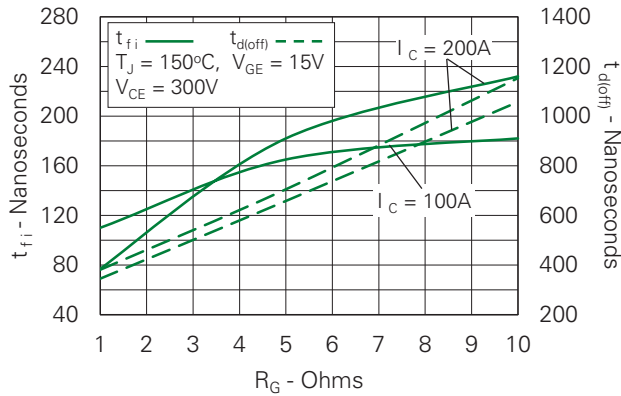


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

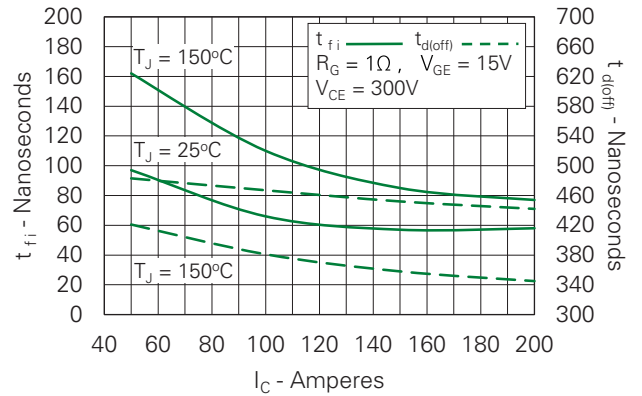


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

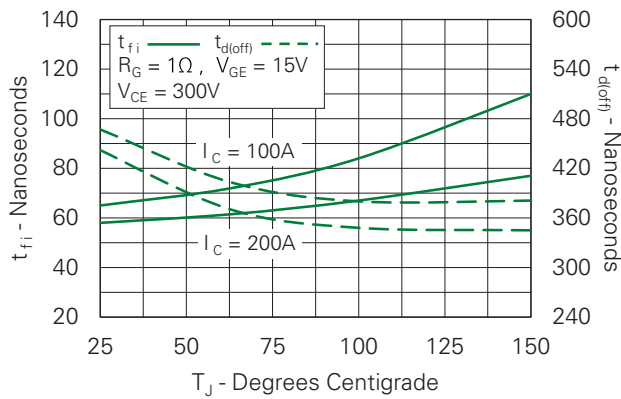


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

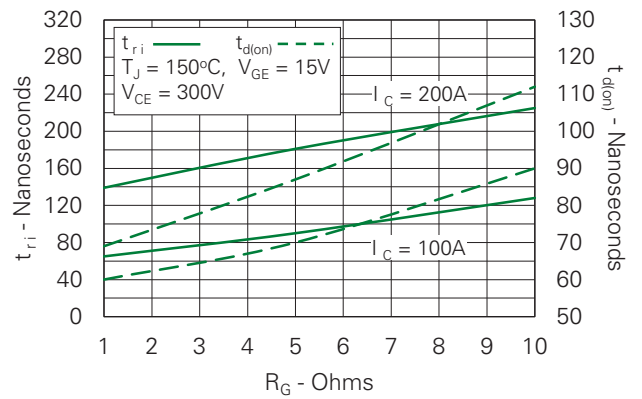


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

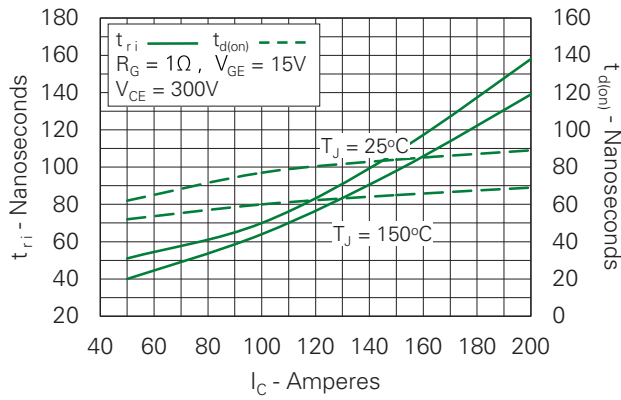


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

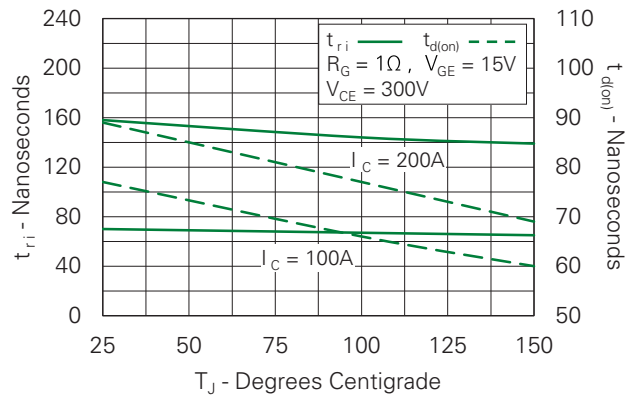
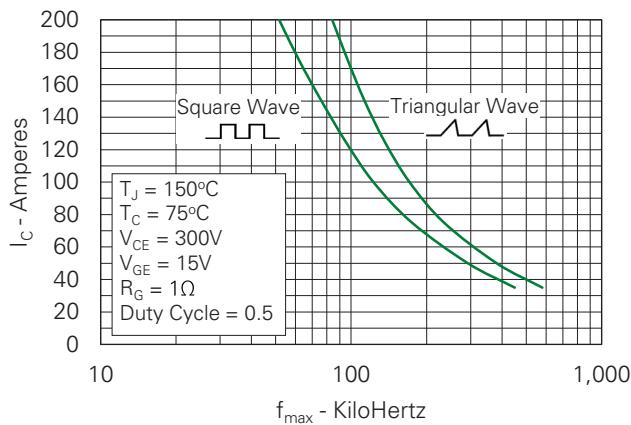
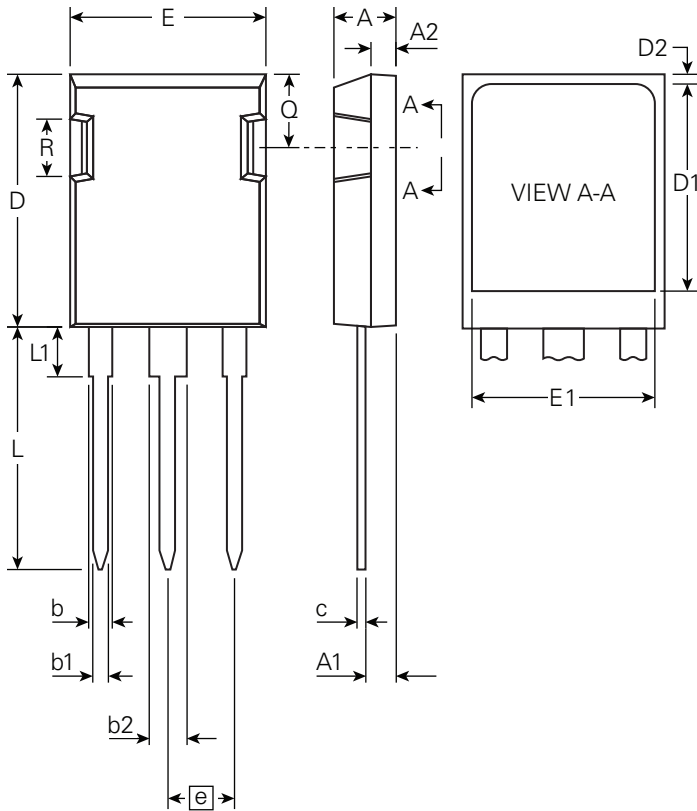


Fig. 21. Maximum Peak Load Current vs. Frequency



Part Outline Drawing (PLUS-247-3L)



Symbol	Inches			Millimeters		
	Min.	Typical	Max.	Min.	Typical	Max.
A	0.190	–	0.205	4.83	–	5.21
A1	0.090	–	0.100	2.29	–	2.54
A2	0.075	–	0.085	1.90	–	2.16
b	0.045	–	0.055	1.14	–	1.40
b1	0.075	–	0.083	1.90	–	2.10
b2	0.115	–	0.123	2.92	–	3.12
C	0.024	–	0.031	0.60	–	0.80
D	0.819	–	0.840	20.80	–	21.34
D1	0.650	–	0.690	16.51	–	17.53
D2	0.035	–	0.050	0.89	–	1.27
E	0.620	–	0.635	15.75	–	16.13
e	0.215 BSC			5.45 BSC		
L	0.780	–	0.799	19.80	–	20.30
L1	0.150	–	0.169	3.80	–	4.30
Q	0.220	–	0.244	5.60	–	6.20
R	0.170	–	0.190	4.32	–	4.83

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